

# Narcs Mestres

## List of Publications by Citations

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

206 papers	3,560 citations	30 h-index	52 g-index
217 ext. papers	3,805 ext. citations	4.1 avg, IF	4.41 L-index

#	Paper	IF	Citations
206	Strong isotropic flux pinning in solution-derived YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7-x</sub> nanocomposite superconductor films. <i>Nature Materials</i> , <b>2007</b> , 6, 367-73	27	509
205	Progress towards all-chemical superconducting YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7</sub> -coated conductors. <i>Superconductor Science and Technology</i> , <b>2006</b> , 19, S13-S26	3.1	199
204	Raman scattering by coupled layer plasmons and in-plane two-dimensional single-particle excitations in multi-quantum-well structures. <i>Physical Review Letters</i> , <b>1986</b> , 56, 2517-2520	7.4	173
203	Chemical solution deposition: a path towards low cost coated conductors. <i>Superconductor Science and Technology</i> , <b>2004</b> , 17, 1055-1064	3.1	117
202	The influence of growth conditions on the microstructure and critical currents of TFA-MOD YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7</sub> films. <i>Superconductor Science and Technology</i> , <b>2005</b> , 18, 1141-1150	3.1	95
201	Anisotropic growth of long isolated graphene ribbons on the C face of graphite-capped 6H-SiC. <i>Physical Review B</i> , <b>2009</b> , 80,	3.3	81
200	Chemical solution route to self-assembled epitaxial oxide nanostructures. <i>Chemical Society Reviews</i> , <b>2014</b> , 43, 2200-25	58.5	78
199	Field-effect mobility temperature modeling of 4H-SiC metal-oxide-semiconductor transistors. <i>Journal of Applied Physics</i> , <b>2006</b> , 100, 114508	2.5	77
198	Multiwavelength excitation Raman scattering analysis of bulk and two-dimensional MoS <sub>2</sub> : vibrational properties of atomically thin MoS <sub>2</sub> layers. <i>2D Materials</i> , <b>2015</b> , 2, 035006	5.9	73
197	Smooth Stress Relief of Trifluoroacetate Metal-Organic Solutions for YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7</sub> Film Growth. <i>Chemistry of Materials</i> , <b>2006</b> , 18, 5897-5906	9.6	64
196	Planar edge termination design and technology considerations for 1.7-kV 4H-SiC PiN diodes. <i>IEEE Transactions on Electron Devices</i> , <b>2005</b> , 52, 2309-2316	2.9	59
195	Precursor Evolution and Nucleation Mechanism of YBa <sub>2</sub> Cu <sub>3</sub> O <sub>x</sub> Films by TFA Metal-Organic Decomposition. <i>Chemistry of Materials</i> , <b>2006</b> , 18, 6211-6219	9.6	55
194	High quality YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7</sub> thin films grown by trifluoroacetates metalorganic deposition. <i>Superconductor Science and Technology</i> , <b>2003</b> , 16, 45-53	3.1	54
193	Hydrostatic-pressure dependence of bound excitons in GaP. <i>Physical Review B</i> , <b>1984</b> , 29, 3398-3407	3.3	47
192	Raman scattering in single-variant spontaneously ordered GaInP <sub>2</sub> . <i>Physical Review B</i> , <b>1996</b> , 53, 12994-13001	3.1	46
191	Intrawell and interwell coupling of plasmons in multilayer modulation-doped GaAs/Al <sub>x</sub> Ga <sub>1-x</sub> As quantum wells. <i>Physical Review B</i> , <b>1989</b> , 39, 12695-12703	3.3	42
190	A field-effect electron mobility model for SiC MOSFETs including high density of traps at the interface. <i>Microelectronic Engineering</i> , <b>2006</b> , 83, 440-445	2.5	41

189	Microscopic and optical investigation of Ge nanoislands on silicon substrates. <i>Nanotechnology</i> , <b>2002</b> , 13, 81-85	3.4	40
188	Low-doped 6H-SiC n-type epilayers grown by sublimation epitaxy. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2000</b> , 77, 50-54	3.1	40
187	Electrosynthesis of the poly(N-vinyl carbazole)/carbon nanotubes composite for applications in the supercapacitors field. <i>European Polymer Journal</i> , <b>2006</b> , 42, 2302-2312	5.2	38
186	Thermal Analysis for Low Temperature Synthesis of Oxide Thin Films from Chemical Solutions. <i>Journal of Physical Chemistry C</i> , <b>2013</b> , 117, 20133-20138	3.8	37
185	Nucleation and mesostrain influence on percolating critical currents of solution derived YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7</sub> superconducting thin films. <i>Physica C: Superconductivity and Its Applications</i> , <b>2012</b> , 482, 58-67	4.3	37
184	Selective epitaxial growth of graphene on SiC. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 123503	3.4	37
183	Early stage formation of graphene on the C face of 6H-SiC. <i>Applied Physics Letters</i> , <b>2008</b> , 93, 263102	3.4	37
182	Influence of porosity on the critical currents of trifluoroacetate-MOD YBa/sub 2/Cu/sub 3/O/sub 7/ films. <i>IEEE Transactions on Applied Superconductivity</i> , <b>2003</b> , 13, 2504-2507	1.8	37
181	Single-Crystalline La <sub>0.7</sub> Sr <sub>0.3</sub> MnO <sub>3</sub> Nanowires by Polymer-Template-Directed Chemical Solution Synthesis. <i>Advanced Materials</i> , <b>2008</b> , 20, 3672-3677	24	36
180	Ni/Ti ohmic and Schottky contacts on 4H-SiC formed with a single thermal treatment. <i>Diamond and Related Materials</i> , <b>2005</b> , 14, 1146-1149	3.5	35
179	Composite structure of wood cells in petrified wood. <i>Materials Science and Engineering C</i> , <b>2005</b> , 25, 119-130	1.3	33
178	Resonant Raman scattering by plasmons and LO phonons near the E1 and E1+ Delta 1 gaps of GaSb. <i>Physical Review B</i> , <b>1987</b> , 36, 7469-7485	3.3	32
177	Rich Phase Behavior in a Supramolecular Conducting Material Derived from an Organogelator. <i>Advanced Functional Materials</i> , <b>2009</b> , 19, 934-941	15.6	30
176	Nanoscale magnetic structure and properties of solution-derived self-assembled La <sub>0.7</sub> Sr <sub>0.3</sub> MnO <sub>3</sub> islands. <i>Journal of Applied Physics</i> , <b>2012</b> , 111, 024307	2.5	27
175	Current status of self-organized epitaxial graphene ribbons on the C face of 6H-SiC substrates. <i>Journal Physics D: Applied Physics</i> , <b>2010</b> , 43, 374011	3	27
174	Aging of Sr <sub>2</sub> FeMoO <sub>6</sub> and related oxides. <i>Materials Research Bulletin</i> , <b>2003</b> , 38, 1477-1486	5.1	27
173	Effects of cap layer on ohmic Ti/Al contacts to Si+ implanted GaN. <i>Applied Surface Science</i> , <b>2009</b> , 255, 6057-6060	6.7	25
172	Barrier inhomogeneities and electrical characteristics of Ni/Ti bilayer Schottky contacts on 4H-SiC after high temperature treatments. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2005</b> , 202, 692-697	1.6	25

171	Characterization of High-k Ta[sub 2]Si Oxidized Films on 4H-SiC and Si Substrates as Gate Insulator. <i>Journal of the Electrochemical Society</i> , <b>2005</b> , 152, G259	3.9	24
170	Enabling electromechanical transduction in silicon nanowire mechanical resonators fabricated by focused ion beam implantation. <i>Nanotechnology</i> , <b>2014</b> , 25, 135302	3.4	23
169	Biaxial texture analysis of YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7</sub> -coated conductors by micro-Raman spectroscopy. <i>Physical Review B</i> , <b>2004</b> , 70,	3.3	23
168	Internal infrared laser deflection system: a tool for power device characterization. <i>Measurement Science and Technology</i> , <b>2004</b> , 15, 1011-1018	2	23
167	Fabrication of monocrystalline 3C-SiC resonators for MHz frequency sensors applications. <i>Sensors and Actuators B: Chemical</i> , <b>2008</b> , 133, 276-280	8.5	22
166	Single crystalline La <sub>0.7</sub> Sr <sub>0.3</sub> MnO <sub>3</sub> molecular sieve nanowires with high temperature ferromagnetism. <i>Journal of the American Chemical Society</i> , <b>2011</b> , 133, 4053-61	16.4	20
165	Growth of monolayer graphene on 8° off-axis 4H-SiC (0001) substrates with application to quantum transport devices. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 093107	3.4	20
164	Valence-band-shape modification due to band coupling in strained quantum wells. <i>Physical Review B</i> , <b>1993</b> , 47, 13926-13929	3.3	20
163	All-chemical high-Jc YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7</sub> multilayers with SrTiO <sub>3</sub> as cap layer. <i>Journal of Materials Research</i> , <b>2006</b> , 21, 1106-1116	2.5	18
162	Structure investigation of BN films grown by ion-beam-assisted deposition by means of polarised IR and Raman spectroscopy. <i>Surface and Coatings Technology</i> , <b>1999</b> , 116-119, 93-99	4.4	18
161	Effects of re-doping on superconducting properties and formation of Hg-1223 superconductors. <i>Physica C: Superconductivity and Its Applications</i> , <b>1999</b> , 328, 257-269	1.3	17
160	Edge-on micro-Raman assessment of trigonal modes in partially ordered GaInP <sub>2</sub> . <i>Physical Review B</i> , <b>1996</b> , 54, 17754-17758	3.3	17
159	Determination of single-particle relaxation time from light scattering spectra in modulation-doped quantum wells. <i>Physical Review B</i> , <b>1987</b> , 36, 1565-1569	3.3	17
158	Light scattering by plasmons in germanium. <i>Physical Review B</i> , <b>1984</b> , 29, 3737-3739	3.3	17
157	Spontaneous in-flight assembly of magnetic nanoparticles into macroscopic chains. <i>Nanoscale</i> , <b>2019</b> , 11, 14194-14202	7.7	16
156	Vertical (La,Sr)MnO <sub>3</sub> Nanorods from Track-Etched Polymers Directly Buffering Substrates. <i>Advanced Functional Materials</i> , <b>2010</b> , 20, 892-897	15.6	16
155	Strain-driven alloying: effect on sizes, shape and photoluminescence of GeSi/Si(001) self-assembled islands. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>2002</b> , 89, 62-65	3.1	16
154	One-Step Route to Iron Oxide Hollow Nanocuboids by Cluster Condensation: Implementation in Water Remediation Technology. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2016</b> , 8, 28599-28606	9.5	16

153	Deposited Thin SiO <sub>2</sub> for Gate Oxide on n-Type and p-Type GaN. <i>Journal of the Electrochemical Society</i> , <b>2010</b> , 157, H1008	3.9	15
152	Nanostructuring of epitaxial graphene layers on SiC by means of field-induced atomic force microscopy modification. <i>Journal of Vacuum Science &amp; Technology B</i> , <b>2009</b> , 27, 3149		15
151	Photoluminescence and Raman analysis of strain and composition in InGaAs/AlGaAs pseudomorphic heterostructures. <i>Semiconductor Science and Technology</i> , <b>1992</b> , 7, 562-566	1.8	15
150	Ferromagnetic 1D oxide nanostructures grown from chemical solutions in confined geometries. <i>Chemical Society Reviews</i> , <b>2014</b> , 43, 2042-54	58.5	14
149	Hot-Spot Detection in Integrated Circuits by Substrate Heat-Flux Sensing. <i>IEEE Electron Device Letters</i> , <b>2008</b> , 29, 1142-1144	4.4	14
148	Steady-state sinusoidal thermal characterization at chip level by internal infrared-laser deflection. <i>Journal Physics D: Applied Physics</i> , <b>2008</b> , 41, 155508	3	14
147	Flash Lamp Supported Deposition of 3C-SiC (FLASiC) – A Promising Technique to Produce High Quality Cubic SiC Layers. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 175-180	0.4	14
146	Chemical solution techniques for epitaxial growth of oxide buffer and YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7</sub> films. <i>Journal of the European Ceramic Society</i> , <b>2004</b> , 24, 1831-1835	6	14
145	Theoretical and experimental investigations of single- and multilayer structures with SiGe nanoislands. <i>Materials Science and Engineering C</i> , <b>2003</b> , 23, 1027-1031	8.3	14
144	Excitonic spectrum of. <i>Physical Review B</i> , <b>1992</b> , 46, 13234-13243	3.3	14
143	Spin relaxation of holes in the split-hole band of InP and GaSb. <i>Physical Review B</i> , <b>1987</b> , 35, 3843-3853	3.3	14
142	Orientational ordering of solution derived epitaxial Gd-doped ceria nanowires induced by nanoscratching. <i>Nanotechnology</i> , <b>2010</b> , 21, 025302	3.4	13
141	Fabrication of complementary metal-oxide-semiconductor integrated nanomechanical devices by ion beam patterning. <i>Journal of Vacuum Science &amp; Technology B</i> , <b>2009</b> , 27, 2691		13
140	Optimisation of junction termination extension for the development of a 2000 V planar 4H-BiC diode. <i>Diamond and Related Materials</i> , <b>2003</b> , 12, 1231-1235	3.5	13
139	Electrochemical Tuning of Metal Insulator Transition and Nonvolatile Resistive Switching in Superconducting Films. <i>ACS Applied Materials &amp; Interfaces</i> , <b>2018</b> , 10, 30522-30531	9.5	12
138	Optical study of boron nitride thin films prepared by plasma-enhanced chemical vapor deposition. <i>Diamond and Related Materials</i> , <b>1997</b> , 6, 1550-1554	3.5	12
137	Analysis of 1.2 kV JBS rectifiers fabricated in 4H-SiC. <i>Semiconductor Science and Technology</i> , <b>2006</b> , 21, 670-676	1.8	12
136	Transmission Fabry-Pérot interference thermometry for thermal characterization of microelectronic devices. <i>Semiconductor Science and Technology</i> , <b>2006</b> , 21, 1537-1542	1.8	12

135	Interface control in all metalorganic deposited coated conductors: Influence on critical currents. <i>Journal of Materials Research</i> , <b>2006</b> , 21, 2176-2184	2.5	12
134	Confocal micro-Raman characterization of lattice damage in high energy aluminum implanted 6H-SiC. <i>Journal of Applied Physics</i> , <b>1999</b> , 85, 99-104	2.5	12
133	Synthesis and characterization of c-BN films prepared by ion beam assisted deposition and triode sputtering. <i>Thin Solid Films</i> , <b>1999</b> , 355-356, 89-95	2.2	12
132	Photoluminescence study of implantation-induced intermixing of In <sub>0.53</sub> Ga <sub>0.47</sub> As/InP single quantum wells by argon ions. <i>Journal of Applied Physics</i> , <b>1993</b> , 74, 1983-1986	2.5	12
131	Fabrication of highly regular suspended graphene nanoribbons through a one-step electron beam lithography process. <i>Microelectronic Engineering</i> , <b>2014</b> , 129, 81-85	2.5	11
130	Direct Monolithic Integration of Vertical Single Crystalline Octahedral Molecular Sieve Nanowires on Silicon. <i>Chemistry of Materials</i> , <b>2014</b> , 26, 1019-1028	9.6	11
129	Damage Reduction in Channeled Ion Implanted 6H-SiC. <i>Materials Science Forum</i> , <b>2000</b> , 338-342, 893-896	0.4	11
128	Lateral spread of implanted ion distributions in 6H-SiC: simulation. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1999</b> , 61-62, 373-377	3.1	11
127	Resonant Raman scattering by spin-density fluctuations in n-type germanium. <i>Physical Review Letters</i> , <b>1985</b> , 55, 1132-1135	7.4	11
126	Spontaneous cationic ordering in chemical-solution-grown La <sub>2</sub> CoMnO <sub>6</sub> double perovskite thin films. <i>NPG Asia Materials</i> , <b>2019</b> , 11,	10.3	10
125	High temperature transformation of electrospun BaZrO <sub>3</sub> nanotubes into nanoparticle chains. <i>CrystEngComm</i> , <b>2011</b> , 13, 7224	3.3	10
124	Highly sensitive strained AlN on Si(111) resonators. <i>Sensors and Actuators A: Physical</i> , <b>2009</b> , 150, 64-68	3.9	10
123	A study of the influence of the annealing processes and interfaces with deposited SiO <sub>2</sub> from tetra-ethoxy-silane for reducing the thermal budget in the gate definition of 4H-SiC devices. <i>Thin Solid Films</i> , <b>2006</b> , 513, 248-252	2.2	10
122	Magneto-optics of narrow GaAs/Al <sub>x</sub> Ga <sub>1-x</sub> As quantum wells grown on vicinal substrates. <i>Physical Review B</i> , <b>1992</b> , 45, 6942-6945	3.3	10
121	Coupled Plasmons and Single Particle Excitations in the Two-Dimensional Electron Gas. <i>Physica Scripta</i> , <b>1987</b> , T19A, 109-119	2.6	10
120	Photoemission electron microscopy study of sub-200 nm self-assembled La <sub>0.7</sub> BrLa <sub>0.3</sub> MnO <sub>3</sub> epitaxial islands. <i>Nanoscale</i> , <b>2013</b> , 5, 2990-8	7.7	9
119	Chemical synthesis of oriented ferromagnetic LaSr <sub>2</sub> Mn manganese oxide molecular sieve nanowires. <i>Chemical Communications</i> , <b>2012</b> , 48, 6223-5	5.8	9
118	Interfacial properties of AlN and oxidized AlN on Si. <i>Surface Science</i> , <b>2010</b> , 604, 63-67	1.8	9

117	Epitaxial nucleation and growth of buffer layers and Y123 coated conductors deposited by metal-organic decomposition. <i>Physica C: Superconductivity and Its Applications</i> , <b>2002</b> , 372-376, 806-809	1.3	9
116	Development of an analog processing circuit for IR-radiation power and noncontact position measurements. <i>Review of Scientific Instruments</i> , <b>2005</b> , 76, 025106	1.7	9
115	Phonon Raman scattering in quantum wires. <i>Solid-State Electronics</i> , <b>1996</b> , 40, 707-710	1.7	9
114	Epitaxial growth and characterization of GaAs/Al/GaAs heterostructures. <i>Surface Science</i> , <b>1990</b> , 228, 16-19	1.8	9
113	Integration of HfO <sub>2</sub> on Si/SiC heterojunctions for the gate architecture of SiC power devices. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 013506	3.4	8
112	CVD oriented growth of carbon nanotubes using AlPO <sub>4</sub> -5 and L type zeolites. <i>Microelectronic Engineering</i> , <b>2008</b> , 85, 1202-1205	2.5	8
111	SiC MOSFETs with thermally oxidized Ta <sub>2</sub> Si stacked on SiO <sub>2</sub> as high-k gate insulator. <i>Microelectronic Engineering</i> , <b>2008</b> , 85, 704-709	2.5	8
110	Room Temperature Implantation and Activation Kinetics of Nitrogen and Phosphorus in 4H-SiC Crystals. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 893-896	0.4	8
109	A Highly Effective Edge Termination Design for SiC Planar High Power Devices. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 1253-1256	0.4	8
108	Optical control of the two-dimensional electron-gas density in modulation-doped quantum wells studied by magnetophotoluminescence. <i>Physical Review B</i> , <b>1993</b> , 48, 1967-1969	3.3	8
107	Charge-density domains in photoexcited quantum-well structures. <i>Surface Science</i> , <b>1990</b> , 228, 88-91	1.8	8
106	Aqueous Chemical Solution Deposition of Functional Double Perovskite Epitaxial Thin Films. <i>Chemistry - A European Journal</i> , <b>2020</b> , 26, 9338-9347	4.8	7
105	Analysis of Excess Carrier Concentration Control in Fast-Recovery High Power Bipolar Diodes at Low Current Densities. <i>Journal of the Electrochemical Society</i> , <b>2010</b> , 157, H711	3.9	7
104	Confocal Raman Microprobe of Lattice Damage in N <sup>+</sup> Implanted 6H-SiC. <i>Materials Science Forum</i> , <b>2000</b> , 338-342, 663-666	0.4	7
103	Infrared and Raman analysis of plasma CVD boron nitride thin films. <i>Diamond and Related Materials</i> , <b>1999</b> , 8, 398-401	3.5	7
102	Electron localization in the disordered conductors TiNiSn and HfNiSn observed by Raman and infrared spectroscopies. <i>Solid State Communications</i> , <b>1994</b> , 91, 779-784	1.6	7
101	Direct Visualization of Current-Stimulated Oxygen Migration in YBaCuO Thin Films. <i>ACS Nano</i> , <b>2020</b> , 14, 11765-11774	16.7	7
100	Thickness-concentration-viscosity relationships in spin-coated metalorganic ceria films containing polyvinylpyrrolidone. <i>Journal of Sol-Gel Science and Technology</i> , <b>2014</b> , 72, 21-29	2.3	6



99	Electronic and magnetic structure of LaSr-2 $\times$ manganese oxide molecular sieve nanowires. <i>Microscopy and Microanalysis</i> , <b>2014</b> , 20, 760-6	0.5	6
98	Petrographic and geochemical evidence for multiphase formation of carbonates in the Martian orthopyroxenite Allan Hills 84001. <i>Meteoritics and Planetary Science</i> , <b>2017</b> , 52, 1030-1047	2.8	6
97	Location of hot spots in integrated circuits by monitoring the substrate thermal-phase lag with the mirage effect. <i>Optics Letters</i> , <b>2010</b> , 35, 2657-9	3	6
96	Thermal calibration procedure for internal infrared laser deflection apparatus. <i>Review of Scientific Instruments</i> , <b>2005</b> , 76, 094905	1.7	6
95	CuPt Ordering Fingerprints of Optical Phonons in Ternary III $\times$ Compound Semiconductors. <i>Physica Status Solidi (B): Basic Research</i> , <b>1999</b> , 215, 121-126	1.3	6
94	Magnetic vortex evolution in self-assembled La <sub>0.7</sub> Sr <sub>0.3</sub> MnO <sub>3</sub> nanoislands under in-plane magnetic field. <i>APL Materials</i> , <b>2014</b> , 2, 076111	5.7	5
93	Synthesis of patterned nanographene on insulators from focused ion beam induced deposition of carbon. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , <b>2012</b> , 30, 03D113	1.3	5
92	SiC MOSFET Channel Mobility Dependence on Substrate Doping and Temperature Considering High Density of Interface Traps. <i>Materials Science Forum</i> , <b>2007</b> , 556-557, 835-838	0.4	5
91	Electrical Characterization of Deposited and Oxidized Ta <sub>2</sub> Si as Dielectric Film for SiC Metal-Insulator-Semiconductor Structures. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 845-848	0.4	5
90	Visible Light Laser Irradiation: a Tool for Implantation Damage Reduction. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 941-944	0.4	5
89	Ta <sub>2</sub> Si Thermal Oxidation: A Simple Route to a High-k Gate Dielectric on 4H-SiC. <i>Electrochemical and Solid-State Letters</i> , <b>2004</b> , 7, F93		5
88	Combined synchrotron x-ray diffraction and micro-Raman for following in situ the growth of solution-deposited YBa <sub>2</sub> Cu <sub>3</sub> O <sub>7</sub> thin films. <i>Journal of Materials Research</i> , <b>2005</b> , 20, 3270-3273	2.5	5
87	Structural and Superconducting Properties of Hg <sub>0.75</sub> Re <sub>0.25</sub> Ba <sub>2</sub> Sr <sub>x</sub> Ca <sub>2</sub> Cu <sub>3</sub> O <sub>8+<math>\delta</math></sub> Superconductors Grown by Sol-Gel and Sealed Quartz Tube Synthesis. <i>Journal of Solid State Chemistry</i> , <b>2001</b> , 161, 355-364	3.3	5
86	Infrared Investigation of Implantation Damage in 6H-SiC. <i>Materials Science Forum</i> , <b>2002</b> , 389-393, 859-862	2.4	5
85	Micro-Raman study of high pressure induced graphite-diamond phase-structural transformation: The role of a nitrogen containing precursor. <i>Journal of Applied Physics</i> , <b>2000</b> , 88, 4875	2.5	5
84	Analysis of Aluminium Ion Implantation Damage into 6H-SiC Epilayers. <i>Materials Science Forum</i> , <b>1998</b> , 264-268, 733-736	0.4	5
83	Confocal micro-Raman scattering and Rutherford backscattering characterization of lattice damage in aluminum implanted 6H-SiC. <i>Diamond and Related Materials</i> , <b>1999</b> , 8, 357-360	3.5	5
82	Formation of Self-Organized Mn <sub>3</sub> O <sub>4</sub> Nano-inclusions in LaMnO <sub>3</sub> Films. <i>Frontiers in Physics</i> , <b>2016</b> , 4,	3.9	5



81	Integration of functional complex oxide nanomaterials on silicon. <i>Frontiers in Physics</i> , <b>2015</b> , 3,	3.9	4
80	3C-SiC films on insulated substrates for high-temperature electrostatic-based resonators. <i>Journal of Micromechanics and Microengineering</i> , <b>2010</b> , 20, 115007	2	4
79	Laser beam deflection-based perimeter scanning of integrated circuits for local overheating location. <i>Journal Physics D: Applied Physics</i> , <b>2009</b> , 42, 012002	3	4
78	Characterisation of YBa <sub>2</sub> Cu <sub>3</sub> O <sub>6+x</sub> films grown by the trifluoro-acetate metal organic decomposition route by infrared spectroscopy. <i>Thin Solid Films</i> , <b>2006</b> , 515, 1607-1611	2.2	4
77	SiC Base Micro-Probe for Myocardial Ischemia Monitoring. <i>Materials Science Forum</i> , <b>2004</b> , 457-460, 1483-1486	1.4	4
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